

Product Overview

NCP5111: Power MOSFET / IGBT Driver, Single Input, Half-Bridge

For complete documentation, see the data sheet.

The NCP5111 is a High Voltage Power gate Driver providing two outputs for direct drive of 2 N-channel power MOSFETs or IGBTs arranged in a half-bridge configuration. It uses the bootstrap technique to insure a proper drive of the High-side power switch.

Features

- High Voltage Range: Up to 600V
- dV/dt Immunity ± 50 V/ns
- Gate Drive Supply Range from 10 V to 20 V
- High and Low Drive Outputs
- Output Source / Sink Current Capability 250 mA / 500 mA
- 3.3 V and 5 V Input Logic Compatible
- Up to Vcc Swing on Input Pins
- Matched Propagation Delays Between Both Channels
- One Input with Internal Fixed Dead Time (650 ns)
- Under Vcc LockOut (UVLO) for Both Channels

For more features, see the data sheet

Applications

- Half Bridge Power Converters

Part Electrical Specifications

Product	Compliance	Status	Type	Number of Drivers	V _{in} Max (V)	V _{CC} Max (V)	Drive Source/Sink Typ (mA)	Rise Time (ns)	Fall Time (ns)	t _p Max (ns)	Package Type
NCP5111DR2G	Pb-free Halide free	Active	MOSFET or IGBT	2	600	23	250 / 500	85	35	170	SOIC-8

Application Diagram

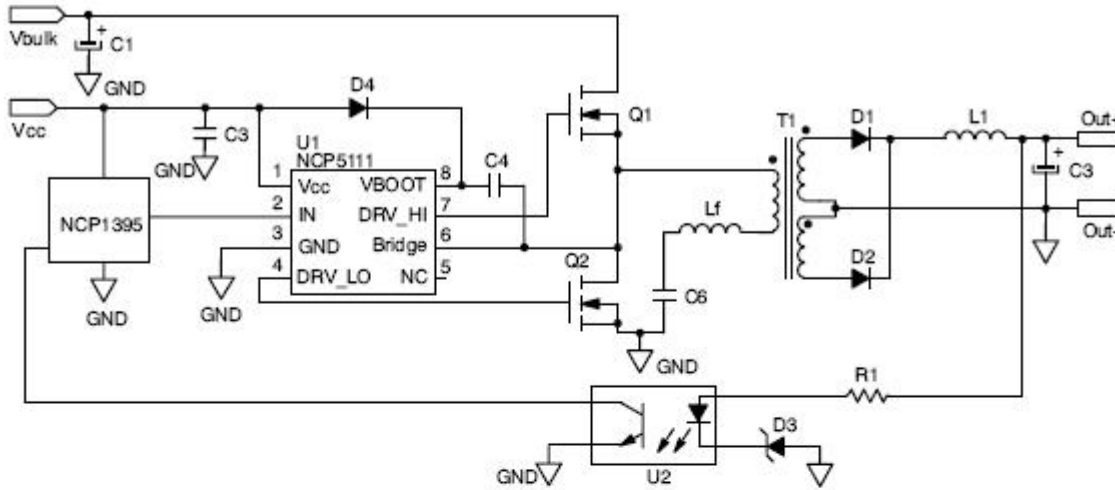


Figure 1. Typical Application Resonant Converter (LLC type)

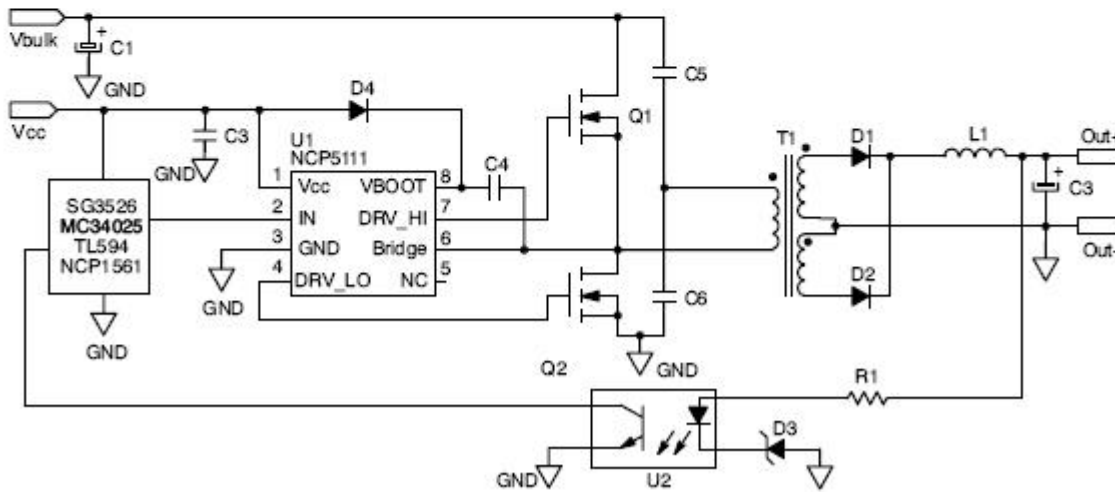


Figure 2. Typical Application Half Bridge Converter

For more information please contact your local sales support at www.onsemi.com.

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